Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S34 3	34	pn near2 soi	US-PGPUB; USPAT	OR	ON	2005/08/10 14:45
S34 2	11	S338 and (@ad<"20040226" or @rlad<"20040226") and ( (diode or p\$1n) same (si\$1ge or (silicon adj germanium) or silicon\$1germanium) )	US-PGPUB; USPAT	OR	ON	2005/08/10 14:46
S34 7	3	S346 and (@ad<"20040226" or @rlad<"20040226") and ( (diode or p\$1n) same (si\$1ge or (silicon adj germanium) or silicon\$1germanium) )	US-PGPUB; USPAT	OR	ON	2005/08/10 14:50
S34 5	15	S344 and (@ad<"20040226" or @rlad<"20040226") and ( (diode or p\$1n) same (si\$1ge or (silicon adj germanium) or silicon\$1germanium) )	US-PGPUB; USPAT	OR	ON	2005/08/10 14:50
S34 9	6	S348 and (@ad<"20040226" or @rlad<"20040226") and ( (diode or p\$1n) same (si\$1ge or (silicon adj germanium) or silicon\$1germanium) )	US-PGPUB; USPAT	OR	ON	2005/08/10 14:51
S35 2	0	S351 not (S349 or S347 or S345)	US-PGPUB; USPAT	OR	ON	2005/08/10 14:52
S35 1	6	S348 and (@ad<"20040226" or @rlad<"20040226") and ( (diode or p\$1n) same (si\$1ge or (silicon ad) germanium) or silicon\$1germanium or ge or germanium) )	US-PGPUB; USPAT	OR	ON	2005/08/10 14:52
S35 0	3	S349 not (S347 or S345)	US-PGPUB; USPAT	OR	ON	2005/08/10 14:52
S34 6	24	( ((pn or diode) near lateral) with (sol or (silicon adj (insulating or insulator or insulation)) )	US-PGPUB; USPAT	OR	ON	2005/08/10 14:57
S31 4	5	S313 and (("257"/\$3.ccls.) or ("438"/\$3.ccls.)) and (diode.ab. or diode.clm.) and (@ad<"20040226" or @rlad<"20040226") and ((ge or germanium).clm.)	US-PGPUB; USPAT	OR	ON	2005/08/10 14:57
S35 4	11	S353 not (S351 or S349 or S347 or S345)	US-PGPUB; USPAT	OR	ON	2005/08/10 14:58
S35 3	17	S348 and (@ad<"20040226" or @rlad<"20040226") and ( (si\$1ge or (silicon adj germanium) or silicon\$1germanium or ge or germanium) )	US-PGPUB; USPAT	OR	ON	2005/08/10 14:59

S35 9	11	S358 and ( (anode or (p adj type) or p\$1type) with (si\$1ge or (silicon adj germanium) or silicon\$1germanium or ge or germanium) )	US-PGPUB; USPAT	OR .	ON	2005/08/10 15:02
S35 6	141	S355 and (@ad<"20040226" or @rlad<"20040226") and ( (si\$1ge or (silicon adj germanium) or silicon\$1germanium or ge or germanium) )	US-PGPUB; USPAT	OR	ON	2005/08/10 15:02
S35 8	45	S357 not (S353 or S351 or S349 or S347 or S345)	US-PGPUB; USPAT	OR	ON	2005/08/10 15:03
S36 1	30	S360 and (@ad<"20040226" or @rlad<"20040226")	US-PGPUB; USPAT	OR	ON	2005/08/10 15:07
S35 7	54	S356 and (("257"/\$3.ccls.) or ("438"/\$3.ccls.)) and (diode.ab. or diode.clm.)	US-PGPUB; USPAT	OR	ON	2005/08/10 15:07
S35 5	1120	( (pn or diode) near2 (lateral or laterally) )	US-PGPUB; USPAT	OR	ON	2005/08/10 15:07
S36 0	30	S355 and ( (anode or (p adj type) or p\$1type) with (si\$1ge or (silicon adj germanium).or silicon\$1germanium or ge or germanium) )	US-PGPUB; USPAT	OR	ON	2005/08/10 15:11
S36 3	42	( (diode near2 (lateral or laterally) ) with (intrinsic or pin))	US-PGPUB; USPAT	OR	ON	2005/08/10 15:13
S36 7	9456	( diode near2 (intrinsic or pin))	US-PGPUB; USPAT	OR	ON	2005/08/10 15:14
S36 6	1	S365 and ( (anode or (p adj type) or p\$1type) with (si\$1ge or (silicon adj germanium) or silicon\$1germanium or ge or germanium))	US-PGPUB; USPAT	OR	ON	2005/08/10 15:14
S36 5	28	S364 and (("257"/\$3.ccls.) or ("438"/\$3.ccls.))	US-PGPUB; USPAT	OR	ON	2005/08/10 15:14
S36 4	41	S363 and (@ad<"20040226" or @rlad<"20040226")	US-PGPUB; USPAT	OR	ON	2005/08/10 15:14
S36 2	13	S361 not (S359 or S353 or S351 or S349 or S347 or S345)	US-PGPUB; USPAT	OR	ON	2005/08/10 15:14
S37 0	37	S369 and ( (anode or (p adj type) or p\$1type) with (si\$1ge or (silicon adj germanium) or silicon\$1germanium ) )	US-PGPUB; USPAT	OR	ON	2005/08/10 15:34
S36 9	1255	S368 and (("257"/\$3.ccls.) or ("438"/\$3.ccls.))	US-PGPUB; USPAT	OR	ON	2005/08/10 15:35
S37 3	112	S372 not S370	US-PGPUB; USPAT	OR	ON	2005/08/10 15:36

S37 1	230	( (pin) with (si\$1ge or (silicon adj germanium) or silicon\$1germanium ) )	US-PGPUB; USPAT	OR	ON	2005/08/10 15:39
S37 2	127	S371 and (("257"/\$3.ccls.) or ("438"/\$3.ccls.))	US-PGPUB; USPAT	OR	ON	2005/08/10 15:40
S36 8	9289	S367 and (@ad<"20040226" or @rlad<"20040226")	US-PGPUB; USPAT	OR	ON	2005/08/10 15:40
S37 5	19	S374 and (@ad<"20040226" or @rlad<"20040226")	US-PGPUB; USPAT	OR	ON	2005/08/10 17:28
S37 4	19	( (pin near diode) same ( (p\$1type or (p adj type)) with (si\$1ge or (silicon adj germanium) or silicon\$1germanium or ge or germanium)) )	US-PGPUB; USPAT	OR	ON	2005/08/10 17:28
S38 1	10	S380 not S376	US-PGPUB; USPAT	OR	ON	2005/08/10 17:29
S37 9	59	S378 and (@ad<"20040226" or @rlad<"20040226")	US-PGPUB; USPAT	OR	ON	2005/08/10 17:34
537 8	61	( (pin near diode) and ( (p\$1type or (p adj type)) with (si\$1ge or (silicon adj germanium) or silicon\$1germanium or ge or germanium)) )	US-PGPUB; USPAT	OR	ON	2005/08/10 17:34
S38 4	12	S383 and ((intrinsic or undoped) near (si or silicon))	US-PGPUB; USPAT	OR	ON	2005/08/10 17:35
S38 0	15	S379 and ((intrinsic or undoped) near (si or silicon))	US-PGPUB; USPAT	OR	ON	2005/08/10 17:35
S38 5	7	S384 not S381	US-PGPUB; USPAT	OR	ON	2005/08/10 17:36
S38 3	142	S382 and (@ad<"20040226" or @rlad<"20040226")	US-PGPUB; USPAT	OR	ON	2005/08/10 17:36
S38 8	18	S387 and (@ad<"20040226" or @rlad<"20040226")	US-PGPUB; USPAT	OR	ON	2005/08/10 17:38
S38 2	143	( (pin near2 (junction or diode)) and ( (p\$1type or (p adj type) or anode) with (si\$1ge or (silicon adj germanium) or silicon\$1germanium )) )	US-PGPUB; USPAT	OR	ON	2005/08/10 17:38
S38 7	18	S386 not (S384 or S381)	US-PGPUB; USPAT	OR	ON	2005/08/10 17:39
S38 6	30	S383 and ((intrinsic or undoped) near2 (si or silicon))	US-PGPUB; USPAT	OR	ON	2005/08/10 17:39
S37 6	15	S375 and (("257"/\$3.ccls.) or ("438"/\$3.ccls.))	US-PGPUB; USPAT	OR	ON	2005/08/10 17:39
S39 8	2	S397 not S394	US-PGPUB; USPAT	OR	ON	2005/08/10 17:42

S39 3	84	S392 not (S386 or S384 or S381)	US-PGPUB; USPAT	OR	ON	2005/08/10 17:42
S40 2	12	S401 not S394	US-PGPUB; USPAT	OR	ON	2005/08/10 17:43
S40 0	13	S393 and ((intrinsic or undoped or (high adj resistance)) with (si or silicon))	US-PGPUB; USPAT	OR	ON	2005/08/10 17:43
S39 9	13	S393 and ((intrinsic or undoped or (high adj resistance)) with(si or silicon))	US-PGPUB; USPAT	OR	ON	2005/08/10 17:43
S39 7	3	S396 and (@ad<"20040226" or @rlad<"20040226")	US-PGPUB; USPAT	OR	ON	2005/08/10 17:43
S39 6	3	S395 not (S386 or S384 or S381)	US-PGPUB; USPAT	OR	ON	2005/08/10 17:43
S39 4	1	S393 and ((intrinsic or undoped or (high adj resistance)) near2 (si or silicon))	US-PGPUB; USPAT	OR	ON	2005/08/10 17:43
S40 6	6	S405 and (@pd<"20040226")	EPO; JPO; DERWENT	OR	ON	2005/08/10 17:48
S40 4	368	( (p\$1type or (p adj type) or anode) with (si\$1ge or (silicon adj germanium) or silicon\$1germanium ) )	EPO; JPO; DERWENT	OR	ON	2005/08/10 17:48
S40 1	13	S400 and (@ad<"20040226" or @rlad<"20040226")	US-PGPUB; USPAT	OR	ON	2005/08/10 17:48
S39 0	150	S389 and (pin with (junction or diode))	US-PGPUB; USPAT	OR	ON	2005/08/10 17:48
S40 9	280	S408 and (("257"/\$3.ccls.) or ("438"/\$3.ccls.))	US-PGPUB; USPAT	OR	ON	2005/08/10 17:51
S39 5	33	S391 and ((intrinsic or undoped or (high adj resistance)) near2 (si or silicon))	US-PGPUB; USPAT	OR	ON	2005/08/10 17:51
S41 1	41	S410 not (S402 or S395 or S386 or S384 or S381)	US-PGPUB; USPAT	OR	ON	2005/08/10 17:52
S41 0	48	S409 and ( (junction or diode or pin).ab.)	US-PGPUB; USPAT	OR	ON	2005/08/10 17:52
S40 3	12	S402 not (S395 or S386 or S384 or S381)	US-PGPUB; USPAT	OR	ON	2005/08/10 17:52
S39 2	105	S391 and (("257"/\$3.ccls.) or ("438"/\$3.ccls.))	US-PGPUB; USPAT	OR	ON	2005/08/10 17:52
S38 9	1561	( (p\$1type or (p adj type) or anode) with (si\$1ge or (silicon adj germanium) or silicon\$1germanium ) )	US-PGPUB; USPAT	OR	ON	2005/08/10 17:56

S41 3	. 32	S412 and ( (pn or diode or pin or junction) same (si\$1ge or (silicon adj germanium) or silicon\$1germanium ) )	US-PGPUB; USPAT	OR	ON	2005/08/10 17:57
S41 5	61	((intrinsic or undoped or (high adj resistance)) near2 (soi or (silicon adj (insulating or insulator or insulation))))	US-PGPUB; USPAT	OR	ON	2005/08/11 18:59
S41 4	92	(soi with ((intrinsic or undoped or (high adj resistance)) near2 (si or silicon)))	US-PGPUB; USPAT	OR	ON	2005/08/11 18:59
S41 2	41	S411 and (("257"/\$3.ccls.) or ("438"/\$3.ccls.))	US-PGPUB; USPAT	OR	ON	2005/08/11 18:59
S40 8	327	S407 and ((intrinsic or undoped or (high adj resistance)) near2 (si or silicon))	US-PGPUB; USPAT	OR	ON	2005/08/11 18:59
S34 4	182	((pn or diode) near2 (soi or (silicon adj (insulating or insulator or insulation)) ) )	US-PGPUB; USPAT	OR	ON	2005/08/11 18:59
S40 5	9	S404 and (pin with (junction or diode))	EPO; JPO; DERWENT	OR	ON	2005/08/11 19:00
S41 9	21	(pin with (junction or diode) with (soi or (silicon adj (insulating or insulator or insulation)) )	US-PGPUB; USPAT	OR	ON	2005/08/11 19:01
S41 8	0	S416 and (pin with (junction or diode) with (soi or (silicon adj (insulating or insulator or insulation))))	US-PGPUB; USPAT	OR	ON	2005/08/11 19:01
S41 7	2	S416 and (pin with (junction or diode))	US-PGPUB; USPAT	OR	ON	2005/08/11 19:01
S41 6	54	S415 and (("257"/\$3.ccls.) or ("438"/\$3.ccls.))	US-PGPUB; USPAT	OR	ON	2005/08/11 19:01
S40 7	1518	S389 and (@ad<"20040226" or @rlad<"20040226")	US-PGPUB; USPAT	OR	ON	2005/08/11 19:01
S42 4	1310	S423 and (("257"/\$3.cor.) or ("438"/\$3.cor.))	US-PGPUB; USPAT	OR	ON	2005/08/11 19:05
S42 0	19	S419 and (@ad<"20040226" or @rlad<"20040226")	US-PGPUB; USPAT	OR	ON	2005/08/11 19:05
S42 6	8	S424 and ( (ge or germanium) with (attractive))	US-PGPUB; USPAT	OR	ON	2005/08/11 19:14
S42 5	226	S424 and ( (ge or germanium) with (provide or providing or better or good))	US-PGPUB; USPAT	OR	ON	2005/08/11 19:14
S42 8	1	S427 not S426	US-PGPUB; USPAT	OR	ON	2005/08/11 19:21
S42 3	1534	S422 and (@ad<"20040226" or @rlad<"20040226")	US-PGPUB; USPAT	OR	ON	2005/08/11 19:21

S42 2	1567	((si or silicon) with (implant or implanted or implantation) with (ge or germanium))	US-PGPUB; USPAT	OR	ON	2005/08/11 19:21
S43 0	29	(((si or silicon) with (implant or implanted or implantation) with (ge or germanium)) same bandgap)	US-PGPUB; USPAT	OR	ON	2005/08/11 19:22
S42 9	1	S428 and (@ad<"20040226" or @rlad<"20040226")	US-PGPUB; USPAT	OR	ON	2005/08/11 19:22
S43 1	29	S430 and (@ad<"20040226" or @rlad<"20040226")	US-PGPUB; USPAT	OR	ON	2005/08/11 19:31
S42 7	5	(((si or silicon) with (implant or implanted or implantation) with (ge or germanium)) same attractive)	US-PGPUB; USPAT	OR	ON.	2005/08/11 19:31
S43 4	23	S433 not S431	US-PGPUB; USPAT	OR	ON	2005/08/11 19:46
S43 3	28	S432 and (@ad<"20040226" or @rlad<"20040226")	US-PGPUB; USPAT	OR	ON	2005/08/11 19:46
S43 8	10	(diode with (sige or si\$1ge or (silicon adj germanium) or silicon\$1germanium) with bandgap)	US-PGPUB; USPAT	OR	ON	2005/08/11 19:57
S43 7	599	(diode with (sige or si\$1ge or (silicon adj germanium) or silicon\$1germanium) )	US-PGPUB; USPAT	OR	ON	2005/08/11 19:57
S43 5	61	(diode with bandgap with (narrow or narrower))	US-PGPUB; USPAT	OR	ON	2005/08/11 19:57
S <del>44</del> 0	10	S439 and (@ad<"20040226" or @rlad<"20040226")	US-PGPUB; USPAT	OR	ON	2005/08/11 19:58
S43 9	10	(diode with (sige or si\$1ge or (silicon adj germanium) or silicon\$1germanium) with bandgap)	US-PGPUB; USPAT	OR	ON	2005/08/11 19:58
S43 6	61	S435 and (@ad<"20040226" or @rlad<"20040226")	US-PGPUB; USPAT	OR	ON	2005/08/11 19:58
S44 2	2	"9953553"	DERWENT	OR	ON	2005/08/11 19:59
544 1	0	WO99/53553	DERWENT	OR	ON	2005/08/11 19:59
S44 3	1	"6417526"	US-PGPUB; USPAT	OR	ON	2005/08/11 20:01
S44 4	0	"6417526" and (intrinsic or pin)	US-PGPUB; USPAT	OR	ON	2005/08/11 20:02
S44 6	0	"6417526" and (undoped or p\$1i\$1n)	US-PGPUB; USPAT	OR	ON	2005/08/11 20:03

S44 5	0	"6417526" and (undoped or pin)	US-PGPUB; USPAT	OR	ON	2005/08/11 20:03
S44 8	110	( ((pn or diode or pin or p-n) near lateral) and (soi or (silicon adj (insulating or insulator or insulation)) )	US-PGPUB; USPAT	OR	ON	2005/08/30 11:09
S44 7	1	"6417526" and (resistance)	US-PGPUB; USPAT	OR	ON	2005/08/30 11:09
S34 8	87	( ((pn or diode) near lateral) and (soi or (silicon adj (insulating or insulator or insulation)) )	US-PGPUB; USPAT	OR	ON	2005/08/30 11:09
S39 1	149	S390 and (@ad<"20040226" or @rlad<"20040226")	US-PGPUB; USPAT	OR	ON	2005/08/30 11:10
S43 2	28	(((si or silicon) with (implant or implanted or implantation) with (ge or germanium)) same diode)	US-PGPUB; USPAT	OR	ON	2005/08/30 11:11
S45 3	6	("3982267"   "4751193"   "5268310"   "5610790"   "5789286"   "5886374").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/30 11:14
S45 2	1	"6426547".pn. and (ge or germanium)	US-PGPUB; USPAT	OR	ON	2005/08/30 11:14
S45 4	0	S453 and (ge or germanium or sige or si\$1ge or silicon\$1germanium)	US-PGPUB; USPAT	OR	ON	2005/08/30 11:15
S45 0	106	S449 and (@ad<"20040226" or @rlad<"20040226")	US-PGPUB; USPAT	OR	ON	2005/08/30 11:15
S42 1	12	S420 and (("257"/\$3.ccls.) or ("438"/\$3.ccls.))	US-PGPUB; USPAT	OR	ON	2005/08/30 11:15
S45 8	- 103	S457 and (("257"/\$3.cor.) or ("438"/\$3.cor.))	US-PGPUB; USPAT	OR	ON	2005/08/30 11:16
S45 7	424	S456 and (@ad<"20040226" or @rlad<"20040226")	US-PGPUB; USPAT	OR	ON	2005/08/30 11:16
S45 6	434	( (ge or germanium or sige or si\$1ge or silicon\$1germanium) with pin)	US-PGPUB; USPAT	OR	ON	2005/08/30 11:16
S45 1	2	(((si or silicon) with (implant or implanted or implantation or implanting) with (ge or germanium))) and S450	US-PGPUB; USPAT	OR	ON	2005/08/30 11:16
S46 3	1	S462 not S461	US-PGPUB; USPAT	OR	ON	2005/08/30 11:17
S46 1	3	(((si or silicon) with (implant or implanted or implantation or implanting) with (ge or germanium)) ) and S460	US-PGPUB; USPAT	OR	ON	2005/08/30 11:17

S46 0	53	S459 and (@ad<"20040226" or @rlad<"20040226") and (("257"/\$3.cor.) or ("438"/\$3.cor.))	US-PGPUB; USPAT	OR	ON	2005/08/30 11:18
S45 9	168	( (sige or si\$1ge or silicon\$1germanium) with pin)	US-PGPUB; USPAT	OR	ON	2005/08/30 11:18
S46 7	5	S466 not (S462 or S461)	US-PGPUB; USPAT	OR	ON	2005/08/30 11:19
S46 5	83	S464 and (@ad<"20040226" or @rlad<"20040226") and (("257"/\$3.cor.) or ("438"/\$3.cor. ))	US-PGPUB; USPAT	OR	ON	2005/08/30 11:20
S46 4	289	( (sige or si\$1ge or silicon\$1germanium) same pin)	US-PGPUB; USPAT	OR	ON	2005/08/30 11:20
S47 1	9	S470 and (lateral with (pn or p-n or diode))	US-PGPUB; USPAT	OR	ON	2005/08/30 11:21
S47 0	62	((implant or implanted or implantation or implanting) with (ge or germanium)) and S469	US-PGPUB; USPAT	OR	ON	2005/08/30 11:21
S46 6	9	((implant or implanted or implantation or implanting) with (ge or germanium)) and S465	US-PGPUB; USPAT	OR	ON	2005/08/30 11:21
S47 2	1	"6426547"	US-PGPUB; USPAT	OR	ON	2005/08/30 12:10
S45 5	1	"6426547".pn. and (ge or germanium or sige or si\$1ge or silicon\$1germanium)	US-PGPUB; USPAT	OR	ON	2005/08/30 12:10
S47 4	187	S473 and (@ad<"20040226" or @rlad<"20040226") and (("257"/\$3.cor.) or ("438"/\$3.cor.))	US-PGPUB; USPAT	OR	ON	2005/08/30 12:11
S46 9	518	S468 and (@ad<"20040226" or @rlad<"20040226") and (("257"/\$3.cor.) or ("438"/\$3.cor.))	US-PGPUB; USPAT	OR	ON	2005/08/30 12:11
S46 8	850	( (sige or si\$1ge or silicon\$1germanium) same (pn or p-n or diode))	US-PGPUB; USPAT	OR	ON	2005/08/30 12:11
S46 2	4	((implant or implanted or implantation or implanting) with (ge or germanium) ) and S460	US-PGPUB; USPAT	OR	ON	2005/08/30 12:11
S47 7	0	(pn or p-n or diode) and S476	US-PGPUB; USPAT	OR	ON	2005/08/30 12:14
S47 3	208	((implant or implanted or implantation or implanting) with (ge or germanium) with (p\$1type or (p adj type)) )	US-PGPUB; USPAT	OR	ON	2005/08/30 12:14

S47 9	22	(sanyo.as.) and (taguchi or hanabusa).in.	US-PGPUB; USPAT	OR	ON	2005/08/30 12:23
S47 8	8	(pn or p-n or diode) and S476	EPO; JPO; DERWENT	OR	ON	2005/08/30 12:23
S47 6	48	((implant or implanted or implantation or implanting) with (ge or germanium) with (p\$1type or (p adj type)) )	EPO; JPO; DERWENT	OR	ON	2005/08/30 12:23
S48 0	0	((implant or implanted or implantation or implanting) with (ge or germanium) ) and S479	US-PGPUB; USPAT	OR	ON	2005/08/30 12:24
S48 5	١ 7	( (pn or p-n or diode).ab.) and S483	US-PGPUB; USPAT	OR	ON	2005/08/30 14:20
S48 1	7	( (pn or p-n or diode).ab.) and S474	US-PGPUB; USPAT	OR	ON	2005/08/30 14:20
S48 6	7	S484 not S485	US-PGPUB; USPAT	OR	ON	2005/08/30 14:21
S48 4	12	( (pn or p-n or diode).clm.) and S483	US-PGPUB; USPAT	OR	ON	2005/08/30 14:25
S48 9	0	( (pn or p-n or diode) near3 lateral) and S483	US-PGPUB; USPAT	OR	ON	2005/08/30 14:26
S48 8	0	( (pn or p-n or diode) near2 lateral) and S483	US-PGPUB; USPAT	OR	ON	2005/08/30 14:26
S48 7	0	( (pn or p-n or diode) near lateral) and S483	US-PGPUB; USPAT	OR	ON	2005/08/30 14:26
S48 2	208	((implant or implanted or implantation or implanting) with (ge or germanium) with (p\$1type or (p adj type)))	US-PGPUB; USPAT	OR	ON	2005/08/30 14:26
S49 3	12	( (pn or p-n or diode) with lateral) and S492	US-PGPUB; USPAT	OR	ON	2005/08/30 14:27
S49 2	568	( (ge or germanium) near3 (p\$1type or (p adj type)) ) and (@ad<"20040226" or @rlad<"20040226") and (("257"/\$3.cor.) or ("438"/\$3.cor. ))	US-PGPUB; USPAT	OR	ON	2005/08/30 14:27
S49 1	0	S490 not ( S484 or S485)	US-PGPUB; USPAT	OR	ON	2005/08/30 14:27
549 6	290	S495 and (@ad<"20040226" or @rlad<"20040226")	US-PGPUB; USPAT	OR	ON	2005/08/30 14:35
S49 5	344	257/616.ccls.	US-PGPUB; USPAT	OR	ON	2005/08/30 14:35
S49 4	12	S493 not (S490 or S484 or S485)	US-PGPUB; USPAT	OR	ON	2005/08/30 14:35
S49 0	2	( (pn or p-n or diode) with lateral) and S483	US-PGPUB; USPAT	OR .	ON	2005/08/30 14:35

S49 9	13	S498 not S497	US-PGPUB; USPAT	OR	ON	2005/08/30 14:36
S49 7	4	( (pn or p-n or diode) with lateral) and S496	US-PGPUB; USPAT	OR	ON	2005/08/30 14:36
S47 5	3	( (sige or si\$1ge or silicon\$1germanium) with (pn or p-n or diode)) and S474	US-PGPUB; USPAT	OR	ON	2005/08/30 14:38
S50 2	13	( (pn or p-n or diode).ab.) and S501	US-PGPUB; USPAT	OR	ON	2005/08/30 14:39
S49 8	13	( (pn or p-n or diode).ab.) and S496	US-PGPUB; USPAT	OR	ON	2005/08/30 14:39
548 3	187	S482 and (@ad<"20040226" or @rlad<"20040226") and (("257"/\$3.cor.) or ("438"/\$3.cor. ))	US-PGPUB; USPAT	OR	ON	2005/08/30 14:39
S50 0	294	( (sige or si\$1ge or silicon\$1germanium) near(p\$1type or (p adj type)) )	US-PGPUB; USPAT	OR	ON	2005/08/30 14:46
S50 5	14	"390606" "1117133"	EPO; DERWENT	OR	ON	2005/08/30 15:07
S50 4	28	S503 not S502	US-PGPUB; USPAT	OR	ON	2005/08/30 15:08
S50 6	1	"6518197"	US-PGPUB; USPAT	OR	ON	2005/08/30 15:10
S50 8	1193	( (sige or si\$1ge or silicon\$1germanium) with (soi or (silicon adj (insulating or insulator or insulation)) )	US-PGPUB; USPAT	OR	ON	2005/08/30 15:11
S50 7	4	"6423989"	US-PGPUB; USPAT	OR	ON	2005/08/30 15:11
S50 1	245	S500 and (@ad<"20040226" or @rlad<"20040226") and (("257"/\$3.cor.) or ("438"/\$3.cor. ))	US-PGPUB; USPAT	OR	ON	2005/08/30 15:11
S44 9	110	( ((pn or diode or pin or p-n) near lateral) and (soi or (silicon adj (insulating or insulator or insulation)) ) )	US-PGPUB; USPAT	OR	ON	2005/08/30 15:11
S51 3	19	S510 not (S503 or S502)	US-PGPUB; USPAT	OR	ON	2005/08/30 15:12
S51 2	19	S510 not (S504 or S502)	US-PGPUB; USPAT	OR	ON	2005/08/30 15:12
S51 1	20	S510 not S504	US-PGPUB; USPAT	OR	ON	2005/08/30 15:12
S50 3	40	S501 and ( (sige or si\$1ge or silicon\$1germanium) with (pn or p-n or diode).)	US-PGPUB; USPAT	OR	ON	2005/08/30 15:12

S51 0	20	S509 and ( (sige or si\$1ge or silicon\$1germanium) with (diode)	US-PGPUB; USPAT	OR	ON	2005/09/18 15:25
S51 4	1	( (sige or si\$1ge or silicon\$1germanium) with (mbe or (molecular adj beam)) with "instead")	US-PGPUB; USPAT	OR	ON	2005/09/18 15:26
S52 1	279	( (si or silicon) with ((implant or implanting or implanted) near (ge or germanium)) )	US-PGPUB; USPAT	OR	ON .	2005/09/18 15:27
S52 0	3	( (si or silicon) with ((implant or implanting or implanted) near (ge or germanium)) with fast)	US-PGPUB; USPAT	OR	ON	2005/09/18 15:27
S51 9	0	( (si or silicon) with ((implant or implanting or implanted) near (ge or germanium)) with cost)	US-PGPUB; USPAT	OR	ON	2005/09/18 15:27
S51 8	0	( (si or silicon) with ((implant or implanting or implanted) near (ge or germanium)) with cheaper)	US-PGPUB; USPAT	OR	ON	2005/09/18 15:27
S51 6	0	( (sige or si\$1ge or silicon\$1germanium) with ((implant or implanting or implanted) near (ge or germanium)) with cost)	US-PGPUB; USPAT	OR	ON	2005/09/18 15:27
S51 5	3	( (sige or si\$1ge or silicon\$1germanium) with ((implant or implanting or implanted) near (ge or germanium)) with "instead" )	US-PGPUB; USPAT	OR	ON	2005/09/18 15:27
S50 9	942	S508 and (@ad<"20040226" or @rlad<"20040226") and (("257"/\$3.cor.) or ("438"/\$3.cor.))	US-PGPUB; USPAT	OR	ON	2005/09/18 15:28
S52 2	245	S521 and (@ad<"20040226" or @rlad<"20040226") and (("257"/\$3.cor.) or ("438"/\$3.cor. ))	US-PGPUB; USPAT	OR	ON	2005/09/18 15:32
S51 7	0	( (sige or si\$1ge or silicon\$1germanium) with ((implant or implanting or implanted) near (ge or germanium)) with cheaper)	US-PGPUB; USPAT	OR	ON	2005/09/18 15:32
S52 5	4	( (sige or si\$1ge or (silicon adj germanium) or silicon\$1germanium) with ((implant or implanting or implanted) near (ge or germanium)) with "known" )	US-PGPUB; USPAT	OR	ON	2005/09/18 16:18

S52 4	101	S523 and (@ad<"20040226" or @rlad<"20040226") and (("257"/\$3.cor.) or ("438"/\$3.cor. ))	US-PGPUB; USPAT	OR	ON	2005/09/18 16:18
S52 3	108	( (sige or si\$1ge or (silicon adj germanium) or silicon\$1germanium) with ((implant or implanting or implanted) near (ge or germanium)) )	US-PGPUB; USPAT	OR	ON	2005/09/18 16:18
S52 9	172	S528 and (@ay<"2000")	US-PGPUB; USPAT	OR	ON	2005/09/18 19:05
S52 6	4	S525 and (@ad<"20040226" or @rlad<"20040226")	US-PGPUB; USPAT	OR	ON	2005/09/18 19:05
S52 7	271	( speed with (pin near diode))	US-PGPUB; USPAT	OR	ON	2005/09/18 19:06
S53 2	9	S531 and (@ad<"20040226" or @rlad<"20040226")	US-PGPUB; USPAT	OR	ON	2005/09/18 19:07